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(71) Applicant: SONY CORP

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(54) BIMOS SEMICONDUCTOR DEVICE AND ITS
MANUFACTURE

(57) Abstract:

PURPOSE: To lower production costs without lowering current driving capability of a bipolar transistor section and regardless of having a high resistance region in a MOS transistor section.

CONSTITUTION: A part of an emitter of a bipolar transistor 62 and wiring of a high resistance load SRAM 61 are formed by a polycrystalline Si layer 53 of the same layer. In a portion to be a resistance element of the wiring of the high resistance load SRAM 61, an SiO₂ layer 65 is formed in a portion in the direction of thickness, thus forming a thinner polycrystalline Si layer 53a. Thus, a smaller number of manufacture processes and hence lower production costs than in the case of forming separate polycrystal Si layers may be realized.

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